

Undervoltage Sensing Circuit

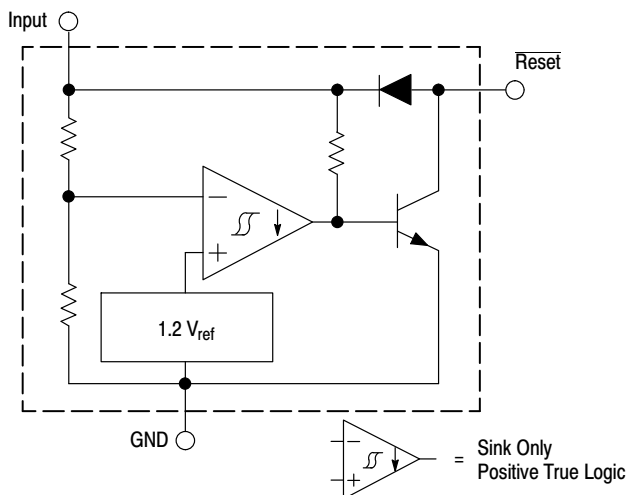
MC34064, MC33064, NCV33064

The MC34064 is an undervoltage sensing circuit specifically designed for use as a reset controller in microprocessor-based systems. It offers the designer an economical solution for low voltage detection with a single external resistor. The MC34064 features a trimmed-in-package bandgap reference, and a comparator with precise thresholds and built-in hysteresis to prevent erratic reset operation. The open collector reset output is capable of sinking in excess of 10 mA, and operation is guaranteed down to 1.0 V input with low standby current. The MC devices are packaged in 3-pin TO-92, micro size TSOP-5, 8-pin SOIC-8 and Micro8 surface mount packages. The NCV device is packaged in SOIC-8 and TO-92.

Applications include direct monitoring of the 5.0 V MPU/logic power supply used in appliance, automotive, consumer and industrial equipment.

Features

- Trimmed-In-Package Temperature Compensated Reference
- Comparator Threshold of 4.6 V at 25°C
- Precise Comparator Thresholds Guaranteed Over Temperature
- Comparator Hysteresis Prevents Erratic Reset
- Reset Output Capable of Sinking in Excess of 10 mA
- Internal Clamp Diode for Discharging Delay Capacitor
- Guaranteed Reset Operation with 1.0 V Input
- Low Standby Current
- Economical TO-92, TSOP-5, SOIC-8 and Micro8 Surface Mount Packages
- NCV Prefix for Automotive and Other Applications Requiring Site and Control Changes
- These Devices are Pb-Free and are RoHS Compliant



This device contains 21 active transistors.

Figure 1. Representative Block Diagram



SOIC-8
D SUFFIX
CASE 751

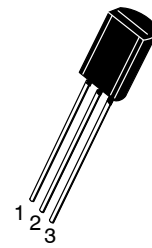


Micro8
DM SUFFIX
CASE 846A

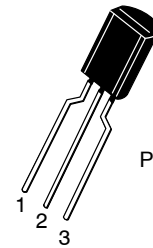


TSOP-5
SN SUFFIX
CASE 483

Pin 1. Ground
2. Input
3. Reset
4. NC
5. NC



STRAIGHT LEAD

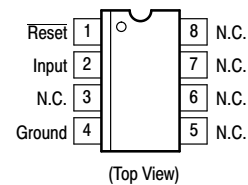


BENT LEAD

TO-92
CASE 29-10

Pin: 1. Reset
2. Input
3. Ground

PIN CONNECTIONS



ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

DEVICE MARKING INFORMATION

See general marking information in the device marking section on page 7 of this data sheet.

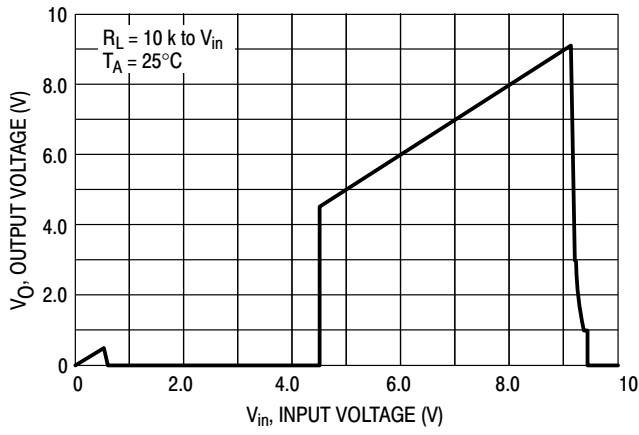


Figure 2. Reset Output Voltage versus Input Voltage

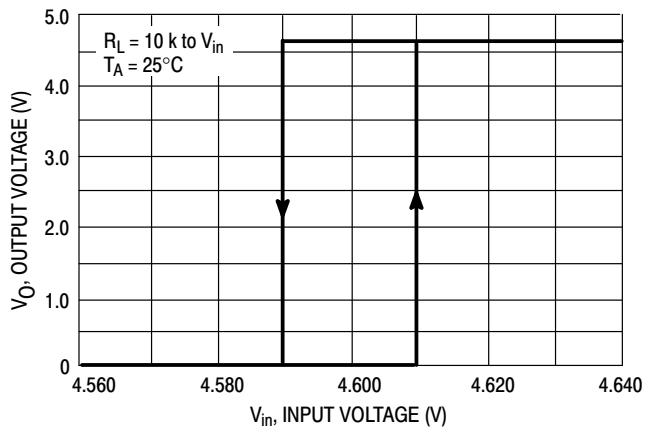


Figure 3. Reset Output Voltage versus Input Voltage

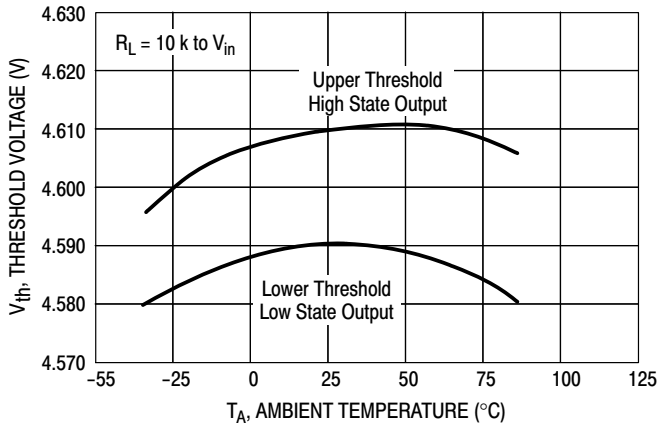


Figure 4. Comparator Threshold Voltage versus Temperature

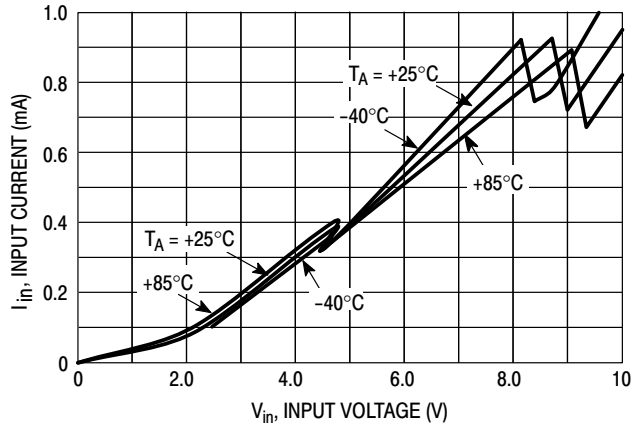


Figure 5. Input Current versus Input Voltage

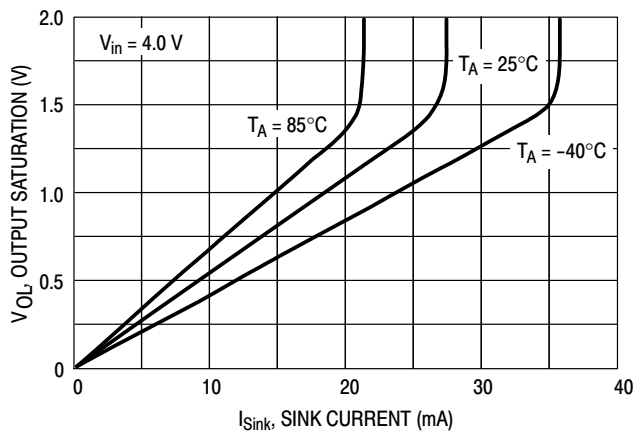


Figure 6. Reset Output Saturation versus Sink Current

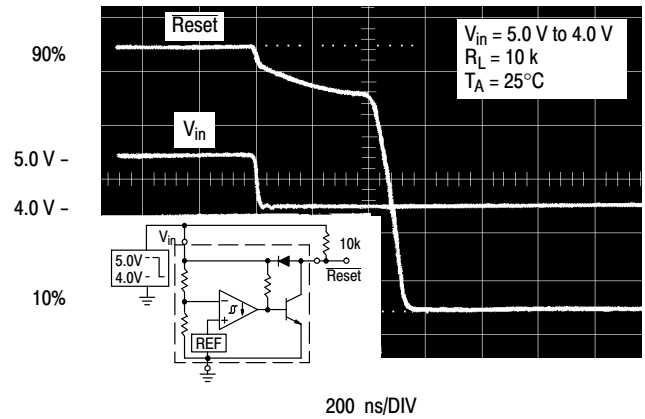


Figure 7. Reset Delay Time

MC34064, MC33064, NCV33064

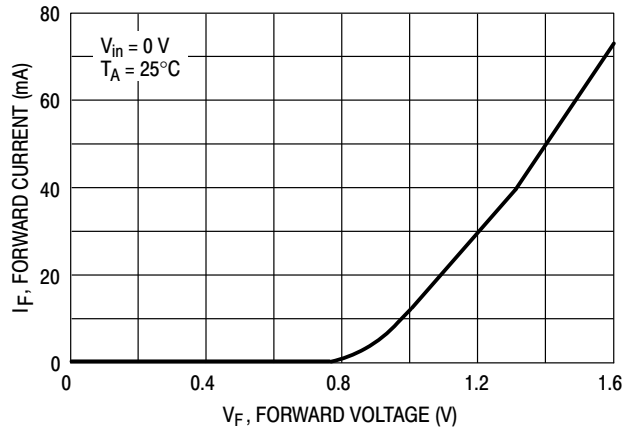


Figure 8. Clamp Diode Forward Current versus Voltage

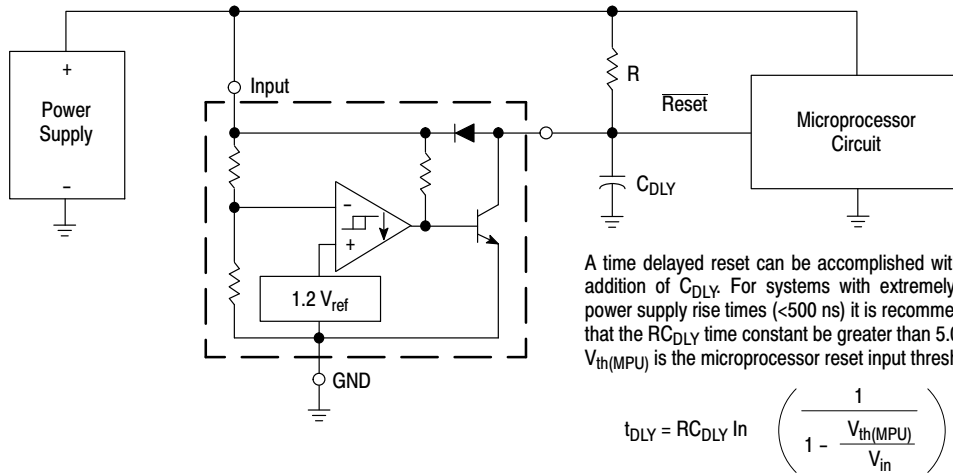
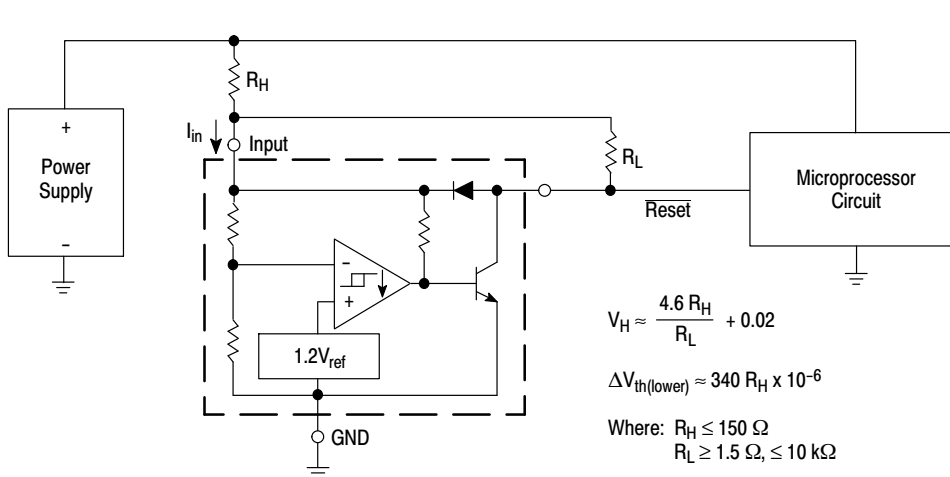


Figure 9. Low Voltage Microprocessor Reset



TEST DATA

| V_H (mV) | ΔV_{th} (mV) | R_H (Ω) | R_L (k Ω) |
|---------------|-------------------------|-----------------------|------------------------|
| 20 | 0 | 0 | 0 |
| 51 | 3.4 | 10 | 1.5 |
| 40 | 6.8 | 20 | 4.7 |
| 81 | 6.8 | 20 | 1.5 |
| 71 | 10 | 30 | 2.7 |
| 112 | 10 | 30 | 1.5 |
| 100 | 16 | 47 | 2.7 |
| 164 | 16 | 47 | 1.5 |
| 190 | 34 | 100 | 2.7 |
| 327 | 34 | 100 | 1.5 |
| 276 | 51 | 150 | 2.7 |
| 480 | 51 | 150 | 1.5 |

Comparator hysteresis can be increased with the addition of resistor R_H . The hysteresis equation has been simplified and does not account for the change of input current I_{in} as V_{CC} crosses the comparator threshold (Figure 4). An increase of the lower threshold $\Delta V_{th(lower)}$ will be observed due to I_{in} which is typically $340\ \mu\text{A}$ at $4.59\ \text{V}$. The equations are accurate to $\pm 10\%$ with R_H less than $150\ \Omega$ and R_L between $1.5\ \text{k}\Omega$ and $10\ \text{k}\Omega$.

Figure 10. Low Voltage Microprocessor Reset with Additional Hysteresis

MC34064, MC33064, NCV33064

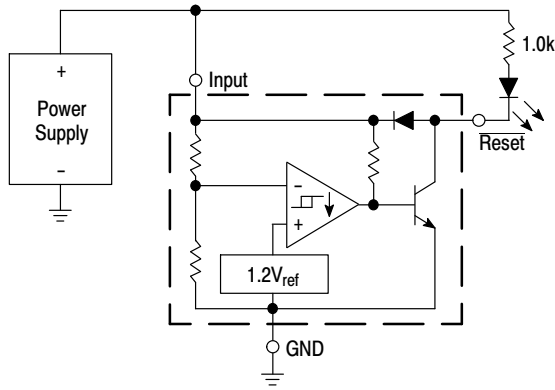


Figure 11. Voltage Monitor

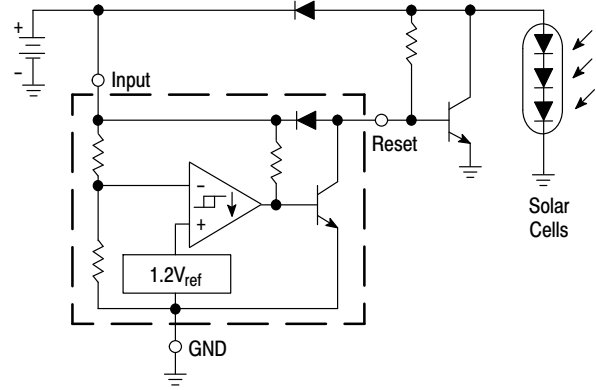
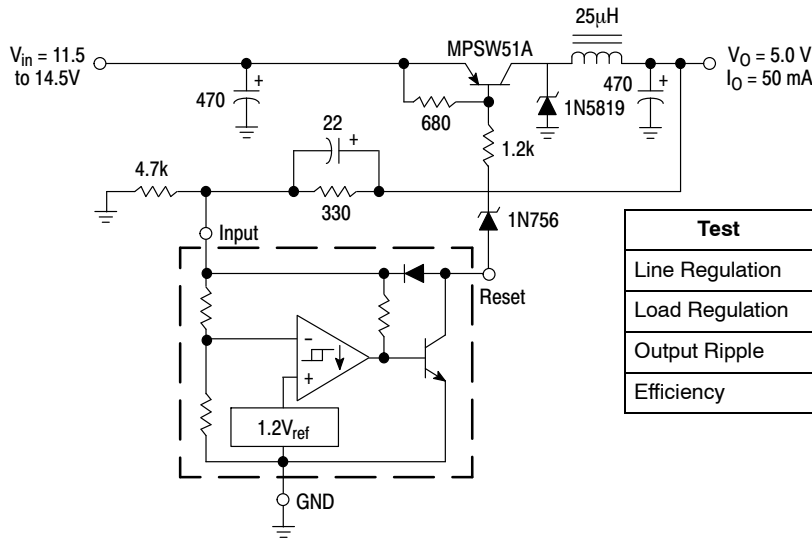
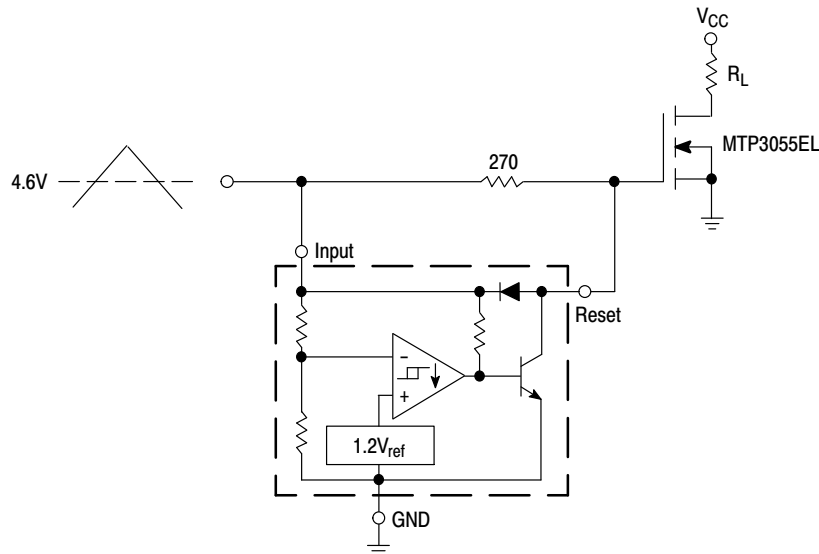


Figure 12. Solar Powered Battery Charger



| Test | Conditions | Results |
|-----------------|---|---------|
| Line Regulation | $V_{in} = 11.5 \text{ V to } 14.5 \text{ V}, I_O = 50 \text{ mA}$ | 35 mV |
| Load Regulation | $V_{in} = 12.6 \text{ V}, I_O = 0 \text{ mA to } 50 \text{ mA}$ | 12 mV |
| Output Ripple | $V_{in} = 12.6 \text{ V}, I_O = 50 \text{ mA}$ | 60 mVpp |
| Efficiency | $V_{in} = 12.6 \text{ V}, I_O = 50 \text{ mA}$ | 77% |

Figure 13. Low Power Switching Regulator



Overheating of the logic level power MOSFET due to insufficient gate voltage can be prevented with the above circuit. When the input signal is below the 4.6 V threshold of the MC34064, its output grounds the gate of the L² MOSFET.

Figure 14. MOSFET Low Voltage Gate Drive Protection

MC34064, MC33064, NCV33064

ORDERING INFORMATION

| Device | Operating Temperature Range | Package | Shipping [†] |
|------------------|----------------------------------|---------------------|--------------------------|
| MC34064D-5G | T _A = 0°C to +70°C | SOIC-8 (Pb-Free) | 98 Units / Rail |
| MC34064D-5R2G | | SOIC-8 (Pb-Free) | 2500 Units/ Tape & Reel |
| MC34064DM-5R2G | | Micro8 (Pb-Free) | 4000 Units / Tape & Reel |
| MC34064P-5G | | TO-92 (Pb-Free) | 2000 Units / Bag |
| MC34064P-5RAG | | TO-92 (Pb-Free) | 2000 Units / Tape & Reel |
| MC34064P-5RPG | | TO-92 (Pb-Free) | 2000 Units / Ammo Pack |
| MC34064P-5RMG | | TO-92 (Pb-Free) | |
| MC34064SN-5T1G | | TSOP-5 (Pb-Free) | 3000 Units / Tape & Reel |
| MC33064D-5G | T _A = -40°C to +85°C | SOIC-8 (Pb-Free) | 98 Units / Rail |
| MC33064D-5R2G | | SOIC-8 (Pb-Free) | 2500 Units / Tape & Reel |
| MC33064DM-5R2G | | Micro8 (Pb-Free) | 4000 Units / Tape & Reel |
| MC33064P-5G | | TO-92 (Pb-Free) | 2000 Units / Bag |
| MC33064P-5RAG | | TO-92 (Pb-Free) | 2000 Units / Tape & Reel |
| MC33064P-5RPG | | TO-92 (Pb-Free) | 2000 Units / Ammo Pack |
| MC33064SN-5T1G | | TSOP-5 (Pb-Free) | 3000 Units / Tape & Reel |
| NCV33064D-5R2G* | T _A = -40°C to +125°C | SOIC-8 (Pb-Free) | 2500 Units / Tape & Reel |
| NCV33064P-5RAG* | | TO-92 (Pb-Free) | 2000 Units / Tape & Reel |
| NCV33064P-5RPG* | | TO-92 (Pb-Free) | 2000 Units / Ammo Pack |
| NCV33064DM-5R2G* | | Micro8 (Pb-Free) | 4000 Units / Tape & Reel |

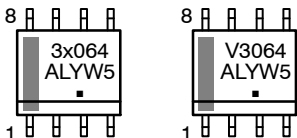
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NCV33064: T_{low} = -40°C, T_{high} = +125°C. Guaranteed by design. NCV prefix is for automotive and other applications requiring site and change control.

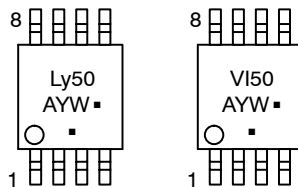
MC34064, MC33064, NCV33064

MARKING DIAGRAMS

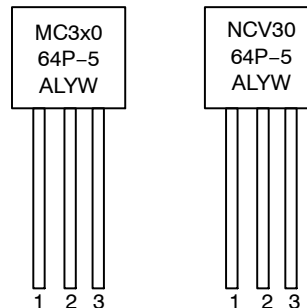
SOIC-8
D SUFFIX
CASE 751



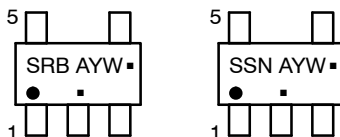
Micro8
DM SUFFIX
CASE 846A



TO-92
P SUFFIX
CASE 029



TSOP-5
SN SUFFIX
CASE 483

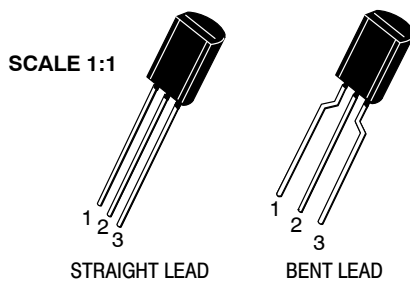


MC34064

MC33064

- x = 3 or 4
- y = C or I
- A = Assembly Location
- L = Wafer Lot
- Y = Year
- W = Work Week
- = Pb-Free Package

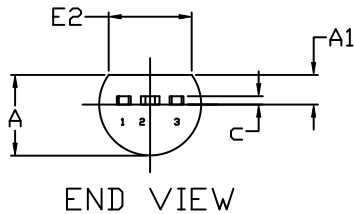
(Note: Microdot may be in either location)



TO-92 (TO-226) 1 WATT
CASE 29-10
ISSUE D

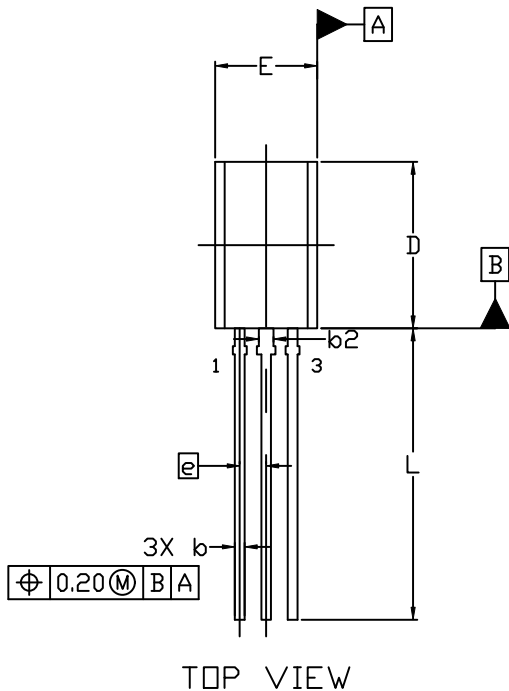
DATE 05 MAR 2021

STRAIGHT LEAD



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR GATE PROTRUSIONS.
4. DIMENSION b AND b2 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 0.20. DIMENSION b2 LOCATED ABOVE THE DAMBAR PORTION OF MIDDLE LEAD.



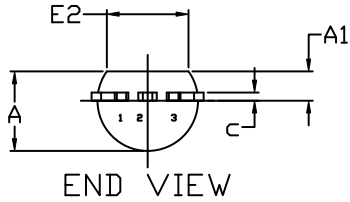
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|-----|-------------|-------|-------|
| | MIN. | NOM. | MAX. |
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| A1 | 1.28 | 1.43 | 1.58 |
| b | 0.38 | 0.465 | 0.55 |
| b2 | 0.62 | 0.70 | 0.78 |
| c | 0.35 | 0.40 | 0.45 |
| D | 7.85 | 8.00 | 8.15 |
| E | 4.75 | 4.90 | 5.05 |
| E2 | 3.90 | --- | --- |
| e | 1.27 BSC | | |
| L | 13.80 | 14.00 | 14.20 |

STYLES AND MARKING ON PAGE 3

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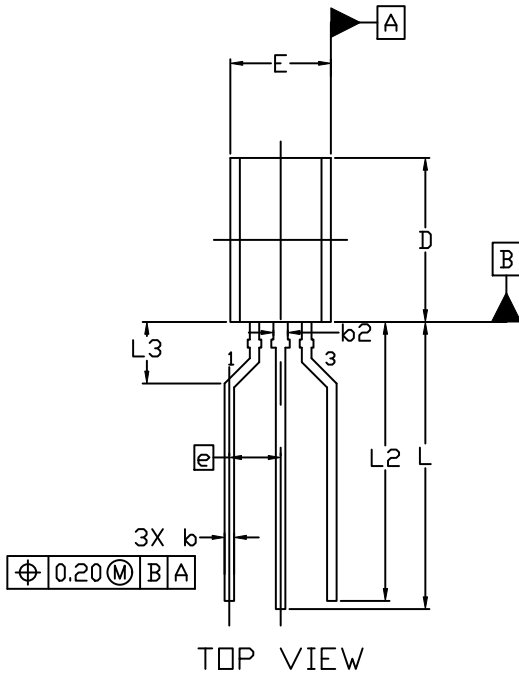
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FORMED LEAD



NOTES:

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2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR GATE PROTRUSIONS.
4. DIMENSION b AND b2 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 0.20. DIMENSION b2 LOCATED ABOVE THE DAMBAR PORTION OF MIDDLE LEAD.



| DIM | MILLIMETERS | | |
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| | MIN. | NOM. | MAX. |
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| b2 | 0.62 | 0.70 | 0.78 |
| c | 0.35 | 0.40 | 0.45 |
| D | 7.85 | 8.00 | 8.15 |
| E | 4.75 | 4.90 | 5.05 |
| E2 | 3.90 | --- | --- |
| e | 2.50 BSC | | |
| L | 13.80 | 14.00 | 14.20 |
| L2 | 13.20 | 13.60 | 14.00 |
| L3 | 3.00 REF | | |

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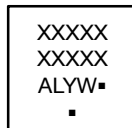
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**TO-92 (TO-226) 1 WATT
CASE 29-10
ISSUE D**

DATE 05 MAR 2021

- | | | | | |
|---|--|--|---|---|
| STYLE 1: PIN 1. EMITTER 2. BASE 3. COLLECTOR | STYLE 2: PIN 1. BASE 2. EMITTER 3. COLLECTOR | STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE | STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE | STYLE 5: PIN 1. DRAIN 2. SOURCE 3. GATE |
| STYLE 6: PIN 1. GATE 2. SOURCE & SUBSTRATE 3. DRAIN | STYLE 7: PIN 1. SOURCE 2. DRAIN 3. GATE | STYLE 8: PIN 1. DRAIN 2. GATE 3. SOURCE & SUBSTRATE | STYLE 9: PIN 1. BASE 1 2. EMITTER 3. BASE 2 | STYLE 10: PIN 1. CATHODE 2. GATE 3. ANODE |
| STYLE 11: PIN 1. ANODE 2. CATHODE & ANODE 3. CATHODE | STYLE 12: PIN 1. MAIN TERMINAL 1 2. GATE 3. MAIN TERMINAL 2 | STYLE 13: PIN 1. ANODE 1 2. GATE 3. CATHODE 2 | STYLE 14: PIN 1. EMITTER 2. COLLECTOR 3. BASE | STYLE 15: PIN 1. ANODE 1 2. CATHODE 3. ANODE 2 |
| STYLE 16: PIN 1. ANODE 2. GATE 3. CATHODE | STYLE 17: PIN 1. COLLECTOR 2. BASE 3. EMITTER | STYLE 18: PIN 1. ANODE 2. CATHODE 3. NOT CONNECTED | STYLE 19: PIN 1. GATE 2. ANODE 3. CATHODE | STYLE 20: PIN 1. NOT CONNECTED 2. CATHODE 3. ANODE |
| STYLE 21: PIN 1. COLLECTOR 2. EMITTER 3. BASE | STYLE 22: PIN 1. SOURCE 2. GATE 3. DRAIN | STYLE 23: PIN 1. GATE 2. SOURCE 3. DRAIN | STYLE 24: PIN 1. EMITTER 2. COLLECTOR/ANODE 3. CATHODE | STYLE 25: PIN 1. MT 1 2. GATE 3. MT 2 |
| STYLE 26: PIN 1. V _{CC} 2. GROUND 2 3. OUTPUT | STYLE 27: PIN 1. MT 2. SUBSTRATE 3. MT | STYLE 28: PIN 1. CATHODE 2. ANODE 3. GATE | STYLE 29: PIN 1. NOT CONNECTED 2. ANODE 3. CATHODE | STYLE 30: PIN 1. DRAIN 2. GATE 3. SOURCE |
| STYLE 31: PIN 1. GATE 2. DRAIN 3. SOURCE | STYLE 32: PIN 1. BASE 2. COLLECTOR 3. EMITTER | STYLE 33: PIN 1. RETURN 2. INPUT 3. OUTPUT | STYLE 34: PIN 1. INPUT 2. GROUND 3. LOGIC | STYLE 35: PIN 1. GATE 2. COLLECTOR 3. EMITTER |

**GENERIC
MARKING DIAGRAM***



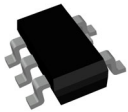
- XXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

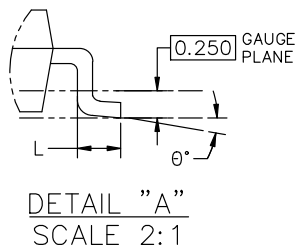
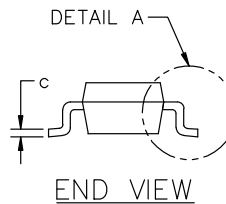
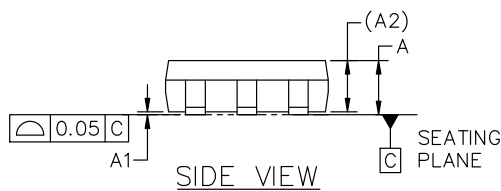
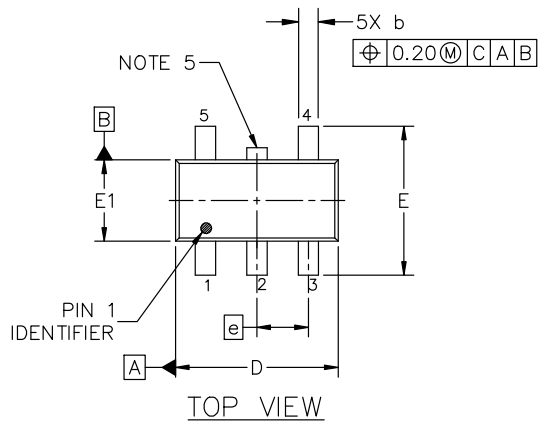
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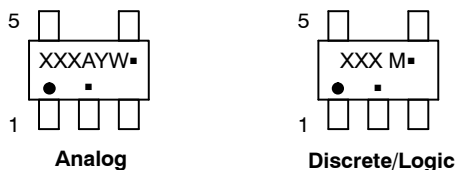


TSOP-5 3.00x1.50x0.95, 0.95P
CASE 483
ISSUE P

DATE 01 APR 2024



GENERIC
MARKING DIAGRAM*



XXX = Specific Device Code XXX = Specific Device Code
A = Assembly Location M = Date Code
Y = Year ■ = Pb-Free Package
W = Work Week

■ = Pb-Free Package

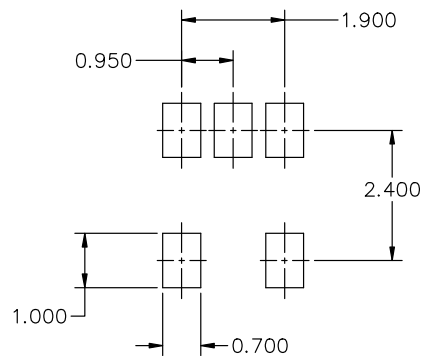
(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
2. ALL DIMENSION ARE IN MILLIMETERS (ANGLES IN DEGREES).
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OF GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSION D.
5. OPTIONAL CONSTRUCTION: AN ADDITIONAL TRIMMED LEAD IS ALLOWED IN THIS LOCATION. TRIMMED LEAD NOT TO EXTEND MORE THAN 0.2 FROM BODY.

| DIM | MILLIMETERS | | |
|----------|-------------|-------|-------|
| | MIN. | NOM. | MAX. |
| A | 0.900 | 1.000 | 1.100 |
| A1 | 0.010 | 0.055 | 0.100 |
| A2 | 0.950 REF. | | |
| b | 0.250 | 0.375 | 0.500 |
| c | 0.100 | 0.180 | 0.260 |
| D | 2.850 | 3.000 | 3.150 |
| E | 2.500 | 2.750 | 3.000 |
| E1 | 1.350 | 1.500 | 1.650 |
| e | 0.950 BSC | | |
| L | 0.200 | 0.400 | 0.600 |
| θ | 0° | 5° | 10° |

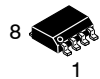


RECOMMENDED MOUNTING FOOTPRINT*

* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERM/D.

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| DESCRIPTION: | TSOP-5 3.00x1.50x0.95, 0.95P | PAGE 1 OF 1 |

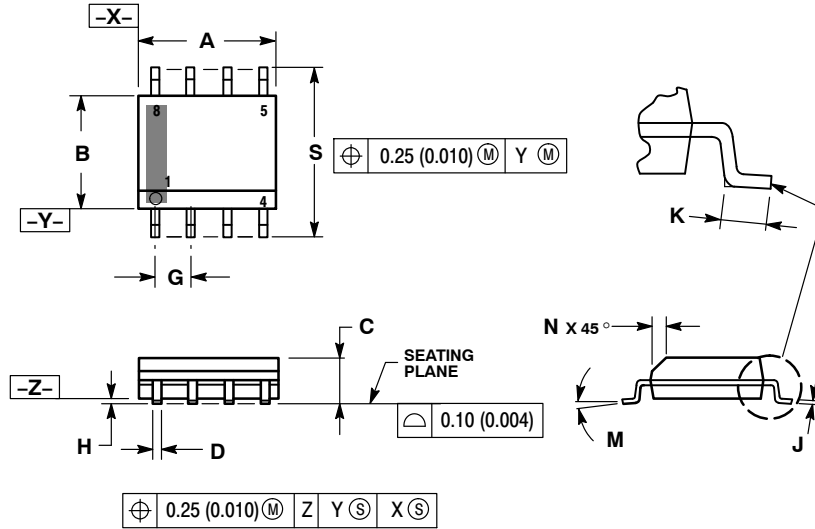
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SCALE 1:1

SOIC-8 NB
CASE 751-07
ISSUE AK

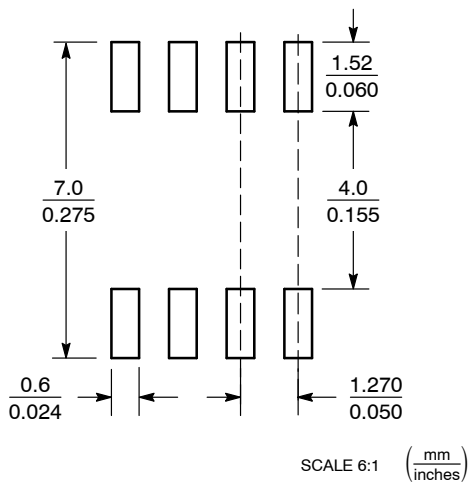
DATE 16 FEB 2011



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
 6. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

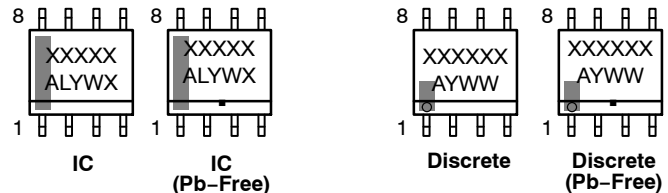
| DIM | MILLIMETERS | | INCHES | |
|-----|-------------|------|-----------|-------|
| | MIN | MAX | MIN | MAX |
| A | 4.80 | 5.00 | 0.189 | 0.197 |
| B | 3.80 | 4.00 | 0.150 | 0.157 |
| C | 1.35 | 1.75 | 0.053 | 0.069 |
| D | 0.33 | 0.51 | 0.013 | 0.020 |
| G | 1.27 BSC | | 0.050 BSC | |
| H | 0.10 | 0.25 | 0.004 | 0.010 |
| J | 0.19 | 0.25 | 0.007 | 0.010 |
| K | 0.40 | 1.27 | 0.016 | 0.050 |
| M | 0° | 8° | 0° | 8° |
| N | 0.25 | 0.50 | 0.010 | 0.020 |
| S | 5.80 | 6.20 | 0.228 | 0.244 |

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb-Free Package

XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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SOIC-8 NB
CASE 751-07
ISSUE AK

DATE 16 FEB 2011

- | | | | |
|---|--|--|--|
| <p>STYLE 1: PIN 1. EMITTER 2. COLLECTOR 3. COLLECTOR 4. EMITTER 5. EMITTER 6. BASE 7. BASE 8. EMITTER</p> | <p>STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 5. BASE, #2 6. EMITTER, #2 7. BASE, #1 8. EMITTER, #1</p> | <p>STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1</p> | <p>STYLE 4: PIN 1. ANODE 2. ANODE 3. ANODE 4. ANODE 5. ANODE 6. ANODE 7. ANODE 8. COMMON CATHODE</p> |
| <p>STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN 4. DRAIN 5. GATE 6. GATE 7. SOURCE 8. SOURCE</p> | <p>STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE</p> | <p>STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd</p> | <p>STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 7. EMITTER, #1 8. COLLECTOR, #1</p> |
| <p>STYLE 9: PIN 1. EMITTER, COMMON 2. COLLECTOR, DIE #1 3. COLLECTOR, DIE #2 4. EMITTER, COMMON 5. EMITTER, COMMON 6. BASE, DIE #2 7. BASE, DIE #1 8. EMITTER, COMMON</p> | <p>STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. BIAS 2 7. INPUT 8. GROUND</p> | <p>STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1</p> | <p>STYLE 12: PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN</p> |
| <p>STYLE 13: PIN 1. N.C. 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN</p> | <p>STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN</p> | <p>STYLE 15: PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON</p> | <p>STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 7. COLLECTOR, DIE #1 8. COLLECTOR, DIE #1</p> |
| <p>STYLE 17: PIN 1. VCC 2. V2OUT 3. V1OUT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC</p> | <p>STYLE 18: PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE</p> | <p>STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1</p> | <p>STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN</p> |
| <p>STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3. CATHODE 3 4. CATHODE 4 5. CATHODE 5 6. COMMON ANODE 7. COMMON ANODE 8. CATHODE 6</p> | <p>STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3. COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND</p> | <p>STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT</p> | <p>STYLE 24: PIN 1. BASE 2. EMITTER 3. COLLECTOR/ANODE 4. COLLECTOR/ANODE 5. CATHODE 6. CATHODE 7. COLLECTOR/ANODE 8. COLLECTOR/ANODE</p> |
| <p>STYLE 25: PIN 1. VIN 2. N/C 3. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT</p> | <p>STYLE 26: PIN 1. GND 2. dv/dt 3. ENABLE 4. ILIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC</p> | <p>STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN</p> | <p>STYLE 28: PIN 1. SW_TO_GND 2. DASIC OFF 3. DASIC_SW_DET 4. GND 5. V_MON 6. VBULK 7. VBULK 8. VIN</p> |
| <p>STYLE 29: PIN 1. BASE, DIE #1 2. EMITTER, #1 3. BASE, #2 4. EMITTER, #2 5. COLLECTOR, #2 6. COLLECTOR, #2 7. COLLECTOR, #1 8. COLLECTOR, #1</p> | <p>STYLE 30: PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1</p> | | |

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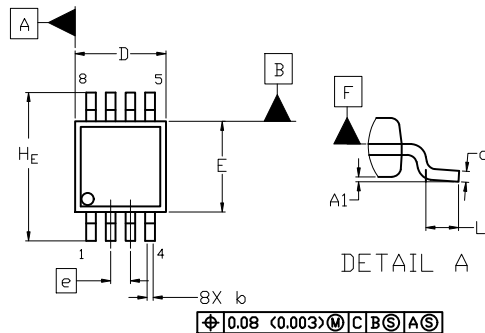
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SCALE 2:1

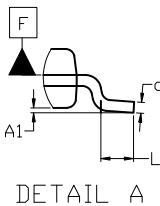
Micro8
CASE 846A-02
ISSUE K

DATE 16 JUL 2020



TOP VIEW

NOTE 3

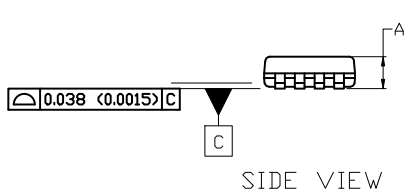


DETAIL A

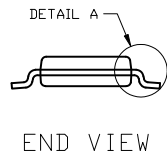
$\phi 0.08$ (0.003) M C B S A S

NOTES:

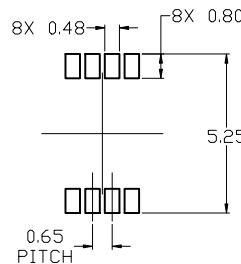
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSION *b* DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.10 mm IN EXCESS OF MAXIMUM MATERIAL CONDITION.
4. DIMENSIONS *D* AND *E* DO NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 mm PER SIDE. DIMENSION *E* DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 mm PER SIDE. DIMENSIONS *D* AND *E* ARE DETERMINED AT DATUM *F*.
5. DATUMS *A* AND *B* ARE TO BE DETERMINED AT DATUM *F*.
6. *A1* IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.



SIDE VIEW



END VIEW

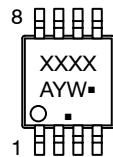


RECOMMENDED MOUNTING FOOTPRINT

| DIM | MILLIMETERS | | |
|----------------------|-------------|------|------|
| | MIN. | NOM. | MAX. |
| A | --- | --- | 1.10 |
| A1 | 0.05 | 0.08 | 0.15 |
| <i>b</i> | 0.25 | 0.33 | 0.40 |
| <i>c</i> | 0.13 | 0.18 | 0.23 |
| <i>D</i> | 2.90 | 3.00 | 3.10 |
| <i>E</i> | 2.90 | 3.00 | 3.10 |
| <i>e</i> | 0.65 BSC | | |
| <i>H_E</i> | 4.75 | 4.90 | 5.05 |
| <i>L</i> | 0.40 | 0.55 | 0.70 |

For additional information on our Pb-Free strategy and soldering details, please download the *DN Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D*.

GENERIC MARKING DIAGRAM*



- XXXX = Specific Device Code
- A = Assembly Location
- Y = Year
- W = Work Week
- = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:

1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 2:

1. SOURCE 1
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. DRAIN 2
7. DRAIN 1
8. DRAIN 1

STYLE 3:

1. N-SOURCE
2. N-GATE
3. P-SOURCE
4. P-GATE
5. P-DRAIN
6. P-DRAIN
7. N-DRAIN
8. N-DRAIN

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